



<b>Oral programme</b>
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Sunday, 04 September 2016	
15:30-18:30	Registration
Room	Foyer Pasteur
16:00-17:30	DCM Tutorial Chair: K. Haenen, <i>Hasselt University and IMEC vzw, Belgium</i> <b>[DCM Tut.] It's all in the surface - the chemistry of diamond</b> A. Krüger, <i>Julius-Maximilians-Universität Würzburg, Germany</i>
Room	Louisville
17:30-18:30	Welcome reception
Room	Foyer Pasteur
Monday, 05 September 2016	
<b>Session 1: Plenary</b> Chair: K. Haenen, <i>Hasselt University and IMEC vzw, Belgium</i>	
Room	Auditorium Einstein
09:00-09:10	Opening address- Welcome: K. Haenen, <i>Hasselt University and IMEC vzw, Belgium</i>
09:10-09:50	<b>[Keynote1] Several decades of single crystal diamond growth by microwave plasma assisted CVD: Breakthroughs and remaining challenges</b> J. Achard, <i>CNRS-Université Paris 13, France</i>
09:50-10:30	<b>[Keynote2] Nanoporous carbons for electrochemical energy storage solutions in supercapacitors</b> F. Béguin, <i>Poznan University of Technology, Poland</i>
10:30-11:00	Refreshment break Room: Foyer Pasteur
<b>Session 2: Diamond power devices</b> Chair: R.J. Nemanich, <i>Arizona State University, USA</i>	
Room	Auditorium Einstein
11:00-11:30	<b>[Inv.01] Diamond electronics realization and substrate issue</b> S. Yamasaki*, T. Makino, D. Takeuchi, M. Ogura, H. Kato, <i>Advanced Power Electronics Research Center, AIST, Japan</i>
11:30-11:45	<b>[O2.1] Unusual frequency dependence of capacitance in oxygen terminated diamond MOS capacitor: The role of the gate leakage current</b> T.T. Pham <sup>1,2</sup> , A. Maréchal <sup>1,2</sup> , N. Rouger <sup>1,2</sup> , D. Eon <sup>1,2</sup> , P. Muret <sup>1,2</sup> , E. Gheeraert <sup>1,2</sup> , J. Pernot* <sup>1,2</sup> , <sup>1</sup> Université Grenoble Alpes, France, <sup>2</sup> CNRS, Institut NÉEL, France, <sup>3</sup> Institut Universitaire de France, France
11:45-12:00	<b>[O2.2] High endurance transparent polycrystalline diamond FET for power electronics application</b> M. Syamsul*, Y. Kitabayashi, D. Matsumura, H. Kawarada, <i>Waseda University, Japan</i>
12:00-12:15	<b>[O2.3] Trade-off for optimizing drift region of diamond power devices</b> G. Chicot* <sup>1,2</sup> , D. Eon <sup>1,2</sup> , N. Rouger <sup>1,2</sup> , <sup>1</sup> Université Grenoble Alpes, France, <sup>2</sup> CNRS, France
12:15-12:30	<b>[O2.4] Sputter deposition AlN and atomic layer deposition Al<sub>2</sub>O<sub>3</sub> as bilayer gate materials for H-terminated diamond field effect transistors</b> R.G. Banal*, M. Imura, J. Liu, M. Liao, Y. Koide, <i>NIMS, Japan</i>
12:30-14:00	Lunch
<b>Session 3: Diamond deposition &amp; doping</b> Chair: J. Pernot, <i>CNRS-Université Grenoble Alpes, France</i>	
Room	Auditorium Einstein
14:00-14:30	<b>[Inv.02] New concept toward freestanding diamond substrate: Overgrowth of bulk diamond on diamond microneedles</b> H. Aida* <sup>1,2</sup> , S-W. Kim <sup>1</sup> , K. Ikejiri <sup>1</sup> , K. Koyama <sup>1</sup> , Y. Kawamata <sup>1</sup> , H. Kodama <sup>3</sup> , A. Sawabe <sup>3</sup> , <sup>1</sup> Namiki Precision Jewel Co. Ltd., Japan, <sup>2</sup> Kyushu University, Japan, <sup>3</sup> Aoyama Gakuin University, Japan
14:30-14:45	<b>[O3.1] Phosphorus incorporation and defect morphology optimisation for n-type diamond growth</b> S.S. Nicley* <sup>1,2</sup> , P. Pobedinskas <sup>1,2</sup> , K. Haenen <sup>1,2</sup> , <sup>1</sup> Hasselt University, Belgium, <sup>2</sup> IMEC, Belgium
14:45-15:00	<b>[O3.2] Diamond etching under high B/C gas ratios</b> A. Fiori*, T. Teraji, <i>National Institute for Materials Science, Japan</i>
15:00-15:15	<b>[O3.3] High speed synthesis of boron doped diamond by in-liquid plasma</b> Y. Sakurai* <sup>1,2</sup> , Y. Harada <sup>2,3</sup> , C. Terashima <sup>1,2</sup> , H. Uetsuka <sup>2,3</sup> , K. Nakata <sup>1,2</sup> , K. Katsumata <sup>1,2</sup> , T. Kondo <sup>1,2</sup> , M. Yuasa <sup>1,2</sup> , A. Fujishima <sup>2</sup> , <sup>1</sup> Tokyo University of Science, Japan, <sup>2</sup> Photocatalysis International Research Center, Japan, <sup>3</sup> Asahi Diamond Industrial Co., Ltd., Japan

15:15-15:30	<b>[O3.4] Approaches for vertical diamond pin-diodes with high blocking voltage and bipolar operation</b> F.A. Koeck, M. Dutta, R. Hathwar, S.M. Goodnick, S. Chowdhury, R.J. Nemanich*, <i>Arizona State University, USA</i>		
15:30-16:00	Refreshment break Room: Foyer Pasteur		
	<b>Focused Session 4: Carbon nitride</b> Chair: C. Donnet, <i>Université Jean Monnet, France</i>		
Room	Auditorium Einstein		
16:00-16:30	<b>[Inv.03] Fullerene-like carbon nitride (CNx) thin films; the effects of doping elements on structure and mechanical resiliency</b> L. Hultman, <i>Linköping University, Sweden</i>		
16:30-16:45	<b>[O4.1] Beta carbon nitride nanoparticles as a new member of the eclectic family of fluorescent carbon nanodots</b> F. Messina* <sup>1</sup> , L. Sciortino <sup>1</sup> , R. Popescu <sup>2</sup> , A. Venezia <sup>3</sup> , A. Sciortino <sup>4</sup> , G. Buscarino <sup>1</sup> , S. Agnello <sup>1</sup> , R. Schneider <sup>2</sup> , D. Gerthsen <sup>2</sup> , M. Cannas <sup>1</sup> , <sup>1</sup> <i>University of Palermo, Italy</i> , <sup>2</sup> <i>Karlsruhe Institute of Technology, Italy</i> , <sup>3</sup> <i>CNR, Italy</i> , <sup>4</sup> <i>University of Catania, Italy</i>		
16:45-17:00	<b>[O4.2] Electrical behaviour at the nanoscale and electrochemical activity of amorphous carbon nitride thin films as a function of their nitrogen content</b> A. Pailleret*, F. Billon, C. Deslouis, <i>Sorbonne Universités, France</i>		
17:00-17:30	<b>[Inv.04] Conductive amorphous carbon nitride thin films for electrochemical electrode at low-temperature deposition by new method: The properties and structures</b> Y. Kikuchi* <sup>1</sup> , K.Y. Inoue <sup>2</sup> , T. Matsue <sup>2</sup> , S. Samukawa <sup>2</sup> , <sup>1</sup> <i>Tokyo Electron Limited, Japan</i> , <sup>2</sup> <i>Tohoku University, Japan</i>		
17:30-19:00	<b>Session 5: Poster session 1</b> Chair: YSA Committee		
Room	Foyer Pasteur		
<b>Tuesday, 06 September 2016</b>			
	<b>Session 6A: Dislocations in diamond</b> Chair: T. Schülke, <i>Fraunhofer Center for Coatings and Diamond Technologies &amp; Michigan State University, USA</i>		<b>Session 6B: Graphene</b> Chair: C.I. Pakes, <i>La Trobe University, Australia</i>
Room	Auditorium Einstein		Sully 1
09:00-09:15	<b>[O6A.1] Dislocation propagation in CVD diamond grown on engineered shape substrates</b> A. Boussadi, A. Tallaire, V. Mille, O. Brinza, J. Achard*, <i>LSPM-CNRS, France</i>	09:00-09:30	<b>[Inv.05] Isotope labelling in multilayered graphene systems</b> M. Kalbáč, <i>Academy of Sciences of the Czech Republic, Czech Republic</i>
09:15-09:30	<b>[YSA.1] Anisotropic stress, mosaic spread and dislocation density of heteroepitaxial diamond on Ir/YSZ/Si(111): Evolution with thickness and underlying mechanisms</b> B-C. Gallheber*, M. Fischer, O. Klein, M. Schreck, <i>University of Augsburg, Germany</i>		
09:30-09:45	<b>[O6A.2] Defect structure of heteroepitaxial diamond grown from grid-patterned nucleation region on Ir</b> K. Ichikawa* <sup>1</sup> , H. Kodama <sup>1</sup> , K. Suzuki <sup>2</sup> , A. Sawabe <sup>1</sup> , <sup>1</sup> <i>Aoyama Gakuin University, Japan</i> , <sup>2</sup> <i>Toplas Engineering Co. Ltd., Japan</i>	09:30-09:45	<b>[O6B.1] Rapid growth of high-quality graphene on Cu (111) surface using C<sub>2</sub>H<sub>2</sub>-based chemical vapour deposition</b> M. Yang*, S. Sasaki, K. Suzuki, H. Miura, <i>Tohoku University, Japan</i>

09:45-10:00	<b>[O6A.3] Fabrication of low defect density single crystalline diamond by two-step epitaxial lateral overgrowth</b> F.N. Li*, W. Wang, Z.C. Liu, Y.F. Wang, S.Y. Li, J. Fu, T.F. Zhu, H.X. Wang, <i>Xi'an Jiaotong University, China</i>	09:45-10:00	<b>[YSA.2] Fabrication of graphene on atomically flat diamond (111) surface using nickel as a catalyst</b> S. Kanada* <sup>1</sup> , M. Nagai <sup>1</sup> , K. Nakanishi <sup>1</sup> , S. Ito <sup>1</sup> , T. Matsumoto <sup>1</sup> , M. Ogura <sup>2</sup> , D. Takeuchi <sup>2</sup> , S. Yamasaki <sup>2</sup> , N. Tokuda <sup>1</sup> , T. Inokuma <sup>1</sup> , <sup>1</sup> <i>Kanazawa University, Japan</i> , <sup>2</sup> <i>AIST, Japan</i>
10:00-10:15	<b>[O6A.4] 3D imaging of defects in high-purity homoepitaxial diamond (100) films</b> T. Teraji*, K. Watanabe, <i>National Institute for Materials Science, Japan</i>	10:00-10:15	<b>[O6B.2] Wafer-scale graphene synthesis and application in flexible and transparent devices</b> C-G. Choi, <i>Electronics and Telecommunications Research Institute (ETRI), Republic of Korea</i>
10:15-10:30	<b>[O6A.5] Disappearance of stacking faults in single crystal diamond by thermal annealing</b> S. Masuya* <sup>1</sup> , T. Moribayashi <sup>1</sup> , K. Hanada <sup>1</sup> , H. Sumiya <sup>2</sup> , M. Kasu <sup>1</sup> , <sup>1</sup> <i>Saga University, Japan</i> , <sup>2</sup> <i>Sumitomo Electric Industries, Ltd., Japan</i>	10:15-10:30	<b>[O6B.3] Frequency response of electrolyte-gated graphene electrodes and transistors</b> S. Drieschner <sup>1</sup> , A. Guimerà <sup>2</sup> , R.G. Cortadella <sup>3</sup> , D. Viana <sup>3</sup> , B.M. Blaschke <sup>1</sup> , J.A. Garrido* <sup>3,4</sup> , <sup>1</sup> <i>Technische Universität München, Germany</i> , <sup>2</sup> <i>Institut de Microelectrònica de Barcelona IMB-CNM (CSIC), Spain</i> , <sup>3</sup> <i>ICN2, Catalan Institute of Nanoscience and Nanotechnology (ICN2), Spain</i> , <sup>4</sup> <i>ICREA, Institució Catalana de Recerca i Estudis Avançats, Spain</i>
10:30-11:00	Refreshment break Room: Foyer Pasteur		
	<b>Session 7A: Diamond deposition methods</b> Chair: M. Schreck, <i>Universität Augsburg, Germany</i>		<b>Session 7B: Characterization of carbon nanostructures I</b> Chair: A. Krüger, <i>Julius-Maximilians-Universität Würzburg, Germany</i>
Room	Auditorium Einstein		Sully 1
11:00-11:15	<b>[O7A.1] Growth and characterization of single crystal diamond by high power DC arcjet with rotating arc root with and without gas recycling</b> F.X. Lu* <sup>1,2</sup> , L.F. Hei <sup>1,2</sup> , Y.M. Tong <sup>1</sup> , G.H. Li <sup>3</sup> , H. Guo <sup>3</sup> , Z.L. Sun <sup>3</sup> , <sup>1</sup> <i>University of Science and Technology Beijing, China</i> , <sup>2</sup> <i>Hebei Plasma Diamond Science and Technology Ltd, China</i> , <sup>3</sup> <i>Beijing Plasma Diamond Technology R&amp;D Ltd, China</i>	11:00-11:30	<b>[Inv.06] Synthesis, structure and tunable electronic properties of pure and doped graphene</b> D.Yu. Usachov, <i>St. Petersburg State University, Russia</i>
11:15-11:30	<b>[O7A.2] Nanocrystalline diamond films deposited at low substrate temperature: From growth process to controlled film properties</b> B. Baudrillart, F. Bénédic*, J. Achard, <i>Université Paris 13, France</i>		

11:30-11:45	<b>[O7A.3] High speed video recording of pulsed discharges for microwave plasma assisted chemical vapor deposition of single crystalline diamond</b> M. Muehle* <sup>1,2</sup> , J. Asmussen <sup>2</sup> , M.F. Becker <sup>1</sup> , T. Stuecken <sup>2</sup> , T. Schuelke <sup>1,2</sup> , <sup>1</sup> Fraunhofer USA Inc., USA, <sup>2</sup> Michigan State University, USA	11:30-11:45	<b>[O7B.1] Sol-gel transition in hydrosols of diamond single crystal nanoparticles</b> A.Y. Vul* <sup>1</sup> , E.D. Eidelman <sup>1,2</sup> , A.E. Aleksenskiy <sup>1</sup> , A.V. Shvidchenko <sup>1</sup> , A.T. Dideikin <sup>1</sup> , V.S. Yuferev <sup>1</sup> , V.T. Lebedev <sup>3</sup> , Y.V. Kul'velis <sup>3</sup> , M.V. Avdeev <sup>4</sup> , <sup>1</sup> Ioffe Physical-Technical Institute, Russia, <sup>2</sup> St. Petersburg State Chemical–Pharmaceutical Academy, Russia, <sup>3</sup> National Research Centre “Kurchatov Institute”, Russia, <sup>4</sup> Joint Institute for Nuclear Research, Russia
11:45-12:00	<b>[O7A.4] Nucleation and growth of polycrystalline diamond films produced by direct-current micro-plasma technique</b> F. Inzoli* <sup>1,2</sup> , F. Ghezzi <sup>2</sup> , R. Caniello <sup>2</sup> , D. Dellasega <sup>1,2</sup> , V. Russo <sup>1</sup> , M. Passoni <sup>1,2</sup> , <sup>1</sup> Politecnico di Milano, Italy, <sup>2</sup> Consiglio Nazionale Delle Ricerche, Italy	11:45-12:00	<b>[O7B.2] Nano-diamond ink formulation with strong photoluminescence properties</b> I. Chernikov <sup>1</sup> , B. Zousman <sup>2</sup> , M. AlAraini <sup>1,3</sup> , R. Arif <sup>1,4</sup> , P. Lutsyk <sup>1</sup> , O. Levinson <sup>2</sup> , A. Rozhin* <sup>1</sup> , <sup>1</sup> Aston University, UK, <sup>2</sup> Ray Techniques LTD, Israel, <sup>3</sup> Al Musanna College of Technology, Oman, <sup>4</sup> University of Sulaimani, Iraq
12:00-12:15	<b>[O7A.5] CVD diamond growth in a microwave plasma with elevated SiH<sub>4</sub> content: From SiV centers to SiC and Si phases formation</b> V.S. Sedov* <sup>1,2</sup> , A.K. Martyanov <sup>1</sup> , V.G. Ralchenko <sup>3,1</sup> , A.A. Khomich <sup>1</sup> , O.N. Poklonskaya <sup>4</sup> , V.I. Konov <sup>1,2</sup> , <sup>1</sup> Russian Academy of Sciences, Russia, <sup>2</sup> National Research Nuclear University MEPhI, Russia, <sup>3</sup> Harbin Institute of Technology, China, <sup>4</sup> Belarusian State University, Belarus	12:00-12:15	<b>[O7B.3] Nanodiamond/oligopeptide composites and assemblies</b> E. Muñoz* <sup>1</sup> , I. Jurewicz <sup>2</sup> , S. Seyedin <sup>3</sup> , J.M. Razal <sup>3</sup> , A.B. Dalton <sup>4,2</sup> , V.L. Cebolla <sup>1</sup> , R. Garriga <sup>5</sup> , <sup>1</sup> Instituto de Carboquímica ICB-CSIC, Spain, <sup>2</sup> University of Surrey, UK, <sup>3</sup> Deakin University, Australia, <sup>4</sup> University of Sussex, UK, <sup>5</sup> Universidad de Zaragoza, Spain
12:15-12:30	 Industry talk by <b>[Industry1] Evaluation results of hetero-epitaxially grown diamond substrate</b> K. Koyama, S-W. Kim, K. Ikejiri, Y. Kawamata, H. Aida*, A. Sawabe, <i>Namiki Precision Jewel Co., Ltd, Japan</i>	12:15-12:30	<b>[O7B.4] NIR fluorescent carbon nano-onions for cellular imaging</b> A. Camisasca*, S. Lettieri, M. D'amora, S. Giordani, <i>Istituto Italiano di Tecnologia (IIT), Italy</i>
12:30-14:00	Lunch		
	<b>Session 8A: Nanodiamond particles</b> Chair: J.C. Arnault, <i>Commissariat à l'énergie atomique et aux énergies alternatives (CEA), France</i>		<b>Focused session 8B: CNTs</b> Chair: M. Kalbáč, <i>CAS-J. Heyrovsky Institute of Physical Chemistry, Czech Republic</i>
Room	Auditorium Einstein		Sully 1
14:00-14:15	<b>[O8A.1] Sulphur functionalized nanodiamond for selective interaction with gold surfaces and biomolecules</b> A. Krueger*, S. Heyer, <i>Wuerzburg University, Germany</i>	14:00-14:15	<b>[O8B.1] Contact thermal resistance of densely-packed VACNTs and deformation mechanics of CNTs</b> Y. Tsukiyama* <sup>1</sup> , T. Kawasaki <sup>1</sup> , I. Nitta <sup>1</sup> , W. Norimatsu <sup>2</sup> , M. Kusunoki <sup>2</sup> , <sup>1</sup> Niigata University, Japan, <sup>2</sup> Nagoya University, Japan

14:15-14:30	<b>[O8A.2] C<sub>3</sub>-induced nanodiamond hydrogenation using molecular hydrogen at low temperature</b> A.I. Ahmed <sup>1</sup> , S. Mandal <sup>2</sup> , O. Williams <sup>2</sup> , C.L. Cheng* <sup>1</sup> , <sup>1</sup> National Dong Hwa University, Taiwan, <sup>2</sup> Cardiff University, UK	14:15-14:30	<b>[O8B.2] Tunable hydrophilicity/hydrophobicity of fluorinated carbon nanotubes via gas-phase grafting of monomers</b> A.P. Kharitonov* <sup>1,2</sup> , J.L. Zha <sup>3,4</sup> , M. Dubois <sup>3,4</sup> , <sup>1</sup> Russian Academy of Sciences, Russia, <sup>2</sup> Tambov State Technical University, Russia, <sup>3</sup> Clermont Université, France, <sup>4</sup> CNRS, France
14:30-14:45	<b>[O8A.3] Ion-exchange properties of detonation nanodiamond and related purity issues</b> P.N. Nesterenko*, A. Peristyy, B. Paull, <i>University of Tasmania, Australia</i>	14:30-14:45	<b>[O8B.3] Influence of CNT oxidation on the mechanical and thermoelectric performance of Cu-CNT composites</b> K.Z. Milowska*, P.D. Bristowe, K. Koziol, <i>University of Cambridge, UK</i>
14:45-15:15	<b>[Inv.07] Fluorescent nanodiamond probes coated in biocompatible polymer shells</b> P. Cigler, <i>Institute of Organic Chemistry and Biochemistry AS CR, v.v.i., Czech Republic</i>	14:45-15:00	<b>[O8B.4] Overcoming the skin effect using carbon nanotube cables</b> G.P. Keeley*, H. Le Poche, A. Ghis, J. Dijon, <i>CEA, France</i>
		15:00-15:15	<b>[O8B.5] Nanodiamonds as hard mask for on-wafer catalyst nanodot preparation: Application to carbon nanotubes growth and field emission applications</b> J-P. Mazellier* <sup>1</sup> , J. Delchevalrie <sup>1</sup> , L. Sabaut <sup>2</sup> , H.A. Girard <sup>3</sup> , S. Saada <sup>3</sup> , <sup>1</sup> Thales Research & Technology, France, <sup>2</sup> Thales Electron Devices, France, <sup>3</sup> CEA-LIST, France
15:15-15:30	 Industry talk by <b>[Industry2] Introducing DAICEL's activities related to detonation nanodiamonds, from the production to unique application developments</b> H. Ito, <i>DAICEL Corporation, Japan</i>	15:15-15:30	<b>[O8B.6] Life-time verification of carbon nanotube-based x-ray tube for commercial use</b> J-W. Jeong* <sup>1</sup> , J-W. Kim <sup>1</sup> , J-T. Kang <sup>1</sup> , M-S. Shin <sup>1,2</sup> , S.R. Park <sup>1</sup> , E.S. Go <sup>1,2</sup> , H.J. Jeon <sup>1,2</sup> , Y-C. Choi <sup>1</sup> , Y-H. Song <sup>1,2</sup> , <sup>1</sup> ETRI, Republic of Korea, <sup>2</sup> UST, Republic of Korea
15:30-16:00	Refreshment break Room: Foyer Pasteur		
	<b>Session 9A: Quantum effects</b> Chair: J.A. Garrido, <i>Catalan Institute of Nanoscience &amp; Nanotechnology (ICN2) and Catalan Institution for Research and Advanced Studies (ICREA), Spain</i>		<b>Session 9B: DLC</b> Chair: J.G. Buijnsters, <i>Delft University of Technology, Netherlands</i>
Room	Auditorium Einstein		Sully 1
16:00-16:30	<b>[Inv.08] Purcell-enhanced single-photon emission from colour centers in diamond coupled to a tunable microcavity</b> D. Hunger* <sup>1,2</sup> , H. Kaupp <sup>1,2</sup> , J. Benedikter <sup>1,2</sup> , T. Hümmer <sup>1,2</sup> , T.W. Hänsch <sup>1,2</sup> , <sup>1</sup> Ludwig-Maximilians-University Munich, Germany, <sup>2</sup> Max-Planck Institute of Quantum Optics, Germany	16:00-16:15	<b>[YSA.3] Understanding carbon/lipid interaction for the rational design of biomaterials</b> J. Vasconcelos*, F. Zen, D. Angione, R. Cullen, P. Colavita, <i>Trinity College Dublin, Ireland</i>
		16:15-16:30	<b>[O9B.1] Correlation of structural and optical properties of PVD grown amorphous carbon thin films</b> I. Solomon V <sup>1</sup> , M. Ranjan <sup>2</sup> , B. Sarma <sup>1</sup> , A. Sarma* <sup>1,2</sup> , <sup>1</sup> VIT University, India, <sup>2</sup> FCIPT Institute for Plasma Research, India

16:30-16:45	<p><b>[YSA.4] Localization of narrowband single photon emitters in nanodiamonds</b> K. Bray*<sup>1</sup>, R. Sandstrom<sup>1</sup>, C. Elbadawi<sup>1</sup>, M. Fischer<sup>2</sup>, M. Schreck<sup>2</sup>, O. Shimoni<sup>1</sup>, C. Lobo<sup>1</sup>, M. Toth<sup>1</sup>, I. Aharonovich<sup>1</sup>, <sup>1</sup>University of Technology Sydney, Australia, <sup>2</sup>Universitat Augsburg, Germany</p>	16:30-16:45	<p><b>[O9B.2] Ultrashort pulse laser microstructuring of diamond-like nanocomposite films</b> E.V. Zavedeev*<sup>1</sup>, M.L. Shupegin<sup>2</sup>, A.D. Barinov<sup>2</sup>, O.S. Zilova<sup>2</sup>, B. Jaeggi<sup>3</sup>, P. Cam<sup>3</sup>, B. Neuenschwander<sup>3</sup>, S.M. Pimenov<sup>1</sup>, <sup>1</sup>General Physics Institute, Russia, <sup>2</sup>National Research University, Russia, <sup>3</sup>Bern University of Applied Sciences, Switzerland</p>
16:45-17:00	<p><b>[O9A.1] Robust luminescence of the silicon-vacancy color center in diamond at high temperatures: Toward thermally-enhanced electroluminescent devices</b> S. Lagomarsino*<sup>1,2</sup>, F. Gorelli<sup>4,5</sup>, M. Santoro<sup>4,5</sup>, N. Fabbri<sup>4,5</sup>, A. Hajeb<sup>5</sup>, S. Sciortino<sup>2,3</sup>, L. Palla<sup>6,7</sup>, C. Czelusniak<sup>2,3</sup>, M. Massi<sup>2</sup>, F. Taccetti<sup>2</sup>, <sup>1</sup>University of Siegen, Germany, <sup>2</sup>INFN-Firenze, Italy, <sup>3</sup>University of Florence, Italy, <sup>4</sup>INO-CNR, Italy, <sup>5</sup>LENS, Italy, <sup>6</sup>University of Pisa, Italy, <sup>7</sup>INFN-Pisa, Italy, <sup>8</sup>Moscow Institute of Physics and Technology, Russia, <sup>9</sup>QSTAR, Italy</p>	16:45-17:15	<p><b>[Inv.09] Recent progress in industrial applications of DLC with focus on ta-C coatings</b> T. Schuelke*<sup>1,2</sup>, V. Weihnacht<sup>3</sup>, W. Fukarek<sup>4</sup>, <sup>1</sup>Michigan State University, USA, <sup>2</sup>Fraunhofer USA, Inc, USA, <sup>3</sup>Fraunhofer Institute for Materials and Beam Technology, Germany, <sup>4</sup>VTD Vakuumtechnik Dresden GmbH, Germany</p>
17:00-17:15	<p><b>[YSA.5] Enhancement of the spin coherence time in NV center induced by an external electric field</b> S. Kobayashi*<sup>1,2</sup>, H. Morishita<sup>3</sup>, Y. Matsuzaki<sup>4</sup>, S. Miwa<sup>1</sup>, Y. Suzuki<sup>1</sup>, N. Mizuochi<sup>2,3</sup>, <sup>1</sup>Osaka University, Japan, <sup>2</sup>JST-CREST, Japan, <sup>3</sup>Kyoto University, Japan, <sup>4</sup>NTT Basic Research Laboratories, Japan</p>		
17:15-17:30	<p><b>[O9A.2] Diamond magnetometry of Meissner currents in a superconducting film</b> N. Alfasi*, S. Masis, O. Shtempeluk, V. Kochetok, E. Buks, <i>Technion Israel Institute of Technology, Israel</i></p>	17:15-17:30	<p><b>[O9B.3] Impacts of substrate bias and dilution gas on the properties of Si-doped diamond-like carbon films by plasma deposition using organosilane as a Si source</b> H. Nakazawa*, S. Miura, <i>Hirosaki University, Japan</i></p>
17:30-18:00	<p><b>[Inv.10] Photoelectric detection of NV centres magnetic resonances in diamond</b> E. Bourgeois*<sup>1,2</sup>, K. Buczak<sup>3</sup>, J. Hruby<sup>1</sup>, M. Trupke<sup>3</sup>, M. Nesladek<sup>1,2</sup>, <sup>1</sup>Hasselt University, Belgium, <sup>2</sup>IMEC, Belgium, <sup>3</sup>Vienna Center for Quantum Science and Technology, Austria</p>	17:30-17:45	<p><b>[O9B.4] Properties of DLC coatings produced in pulsed glow-discharge processes on nitrided and carbonitrided austenitic steel</b> T. Borowski*<sup>1</sup>, M. Dubek<sup>1</sup>, K. Kowalczyk<sup>1</sup>, K. Rozniatowski<sup>1</sup>, K. Kulikowski<sup>1</sup>, M. Spychalski<sup>1</sup>, B. Adamczyk-Cieslak<sup>1</sup>, B. Rajchel<sup>2</sup>, <sup>1</sup>Warsaw University of Technology, Poland, <sup>2</sup>Polish Academy of Sciences, Poland</p>
		17:45-18:00	<p><b>[O9B.5] Influence of amorphous carbon layers on tribological properties of PEEK composite in contact with nitrided layer produced on Ti6Al4V titanium alloy</b> M. Tarnowski*<sup>1</sup>, K. Kulikowski<sup>1</sup>, T. Borowski<sup>1</sup>, B. Rajchel<sup>2</sup>, T. Wierzchon<sup>1</sup>, <sup>1</sup>Warsaw University of Technology, Poland, <sup>2</sup>Institute of Nuclear Physics, Poland</p>
Wednesday, 07 September 2016			

<b>Focused Session 10: Characterization of carbon nanostructures II</b> Chair: A.Ya. Vul', <i>Ioffe Physical Technical Institute, Russia</i>			
Room	Auditorium Einstein		
09:00-09:30	<b>[Inv.11] Nanostructures &amp; nanochemistry at carbon/carbon-related material surfaces, sub-surfaces and interfaces</b> P.G. Soukiassian <sup>1,2</sup> , <sup>1</sup> CEA-Saclay, France, <sup>2</sup> Université de Paris-Sud, France		
09:30-09:45	<b>[O10.1] Wrinkling the graphene: Control of topography by nanoparticles and fullerenes</b> J.K. Vejpravova*, B. Pacakova, A. Mantlikova, T. Verhagen, V. Vales, O. Frank, M. Kalbac, <i>Czech Academy of Sciences, Czech Republic</i>		
09:45-10:00	<b>[O10.2] Is carbon nanotube side-wall really functionalized?</b> X. Devaux* <sup>1,2</sup> , N. Allali <sup>1,2</sup> , V. Mamane <sup>3,2</sup> , M. Dossot <sup>1,2</sup> , <sup>1</sup> Université de Lorraine, France, <sup>2</sup> CNRS, France, <sup>3</sup> Université de Strasbourg, France		
10:00-10:15	<b>[O10.3] Luminescence dynamics of annealed nanodiamonds</b> J. Salava* <sup>1</sup> , F. Trojánek <sup>1</sup> , S. Stehlík <sup>2</sup> , B. Rezek <sup>2,3</sup> , P. Malý <sup>1</sup> , <sup>1</sup> Charles University in Prague, Czech Republic, <sup>2</sup> Czech Academy of Sciences, Czech Republic, <sup>3</sup> Czech Technical University, Czech Republic		
10:15-10:30	<b>[O10.4] Towards large scale preparation of carbon nanostructures in molten salts</b> A.R. Kamali*, D.J. Fray, <i>University of Cambridge, UK</i>		
10:30-11:00	Refreshment break Room: Foyer Pasteur		
	<b>Session 11A: High pressure</b> Chair: M. Kasu, <i>Saga University, Japan</i>		<b>Session 11B: 2D Materials</b> Chair: P. Soukiassian, <i>Commissariat à l'énergie atomique et aux énergies alternatives (CEA), France</i>
Room	Auditorium Einstein		Sully 1
11:00-11:30	<b>[Inv.12] Advanced ultra-hard nanopolycrystalline diamond</b> H. Sumiya*, K. Ikeda, K. Arimoto, K. Harano, <i>Sumitomo Electric Industries, LTD., Japan</i>	11:00-11:15	<b>[O11B.1] Pyridinic dominance nitrogen doped graphene by femtosecond pulsed laser deposition</b> C. Maddi <sup>1</sup> , T. Tite <sup>1</sup> , V. Barnier <sup>2</sup> , A.S. Loir <sup>1</sup> , F. Bourquard <sup>1</sup> , W. Wolski <sup>2</sup> , C. Donnet* <sup>1</sup> , F. Garrelie <sup>1</sup> , <sup>1</sup> Université de Lyon, France, <sup>2</sup> Ecole Nationale Supérieure des Mines de St-Etienne, France
		11:15-11:30	<b>[O11B.2] Lessons learned from carbon nanotube growth can be applied to graphene: 100% reproducibility and improved graphene quality by preheating precursor gases using thermal chemical vapor deposition</b> G.D. Nessim, <i>Bar Ilan University, Israel</i>
11:30-11:45	<b>[O11A.1] A new approach for HPHT synthesis of diamond from graphite</b> S.V. Kidalov, F.M. Shakhov, V.Y. Davydov, V.V. Sokolov, A.Y. Vul*, <i>Ioffe Physical-Technical Institute, Russia</i>	11:30-11:45	<b>[O11B.3] An electrochemical understanding of the graphite oxidation and graphene oxide reduction to produce graphene flakes or films</b> F. Avril* <sup>1,2</sup> , M. Guillot <sup>2</sup> , B. Sala <sup>2</sup> , A. Pailleret <sup>3</sup> , T. Michel <sup>1</sup> , A. Foucaran <sup>1</sup> , <sup>1</sup> Université Montpellier, France, <sup>2</sup> éMa SAS, France, <sup>3</sup> Université Paris 06, France
11:45-12:00	<b>[O11A.2] Synthesis of high-purity sp<sup>3</sup> network polymer and its controlled conversion to nanodiamonds by high pressure high temperature</b> T. Yanase* <sup>1</sup> , K. Hasegawa <sup>1</sup> , T. Nagahama <sup>1</sup> , T. Taniguchi <sup>2</sup> , F. Kawamura <sup>2</sup> , T. Shimada <sup>1</sup> , <sup>1</sup> Hokkaido University, Japan, <sup>2</sup> National Institute for Material Science, Japan	11:45-12:00	<b>[O11B.4] Hydrogen peroxide sensor based on vertical nanographene platform</b> M. Hiramatsu* <sup>1</sup> , M. Tomatsu <sup>1</sup> , H. Kondo <sup>2</sup> , M. Hori <sup>2</sup> , J.S. Foord <sup>3</sup> , <sup>1</sup> Meijo University, Japan, <sup>2</sup> Nagoya University, Japan, <sup>3</sup> University of Oxford, UK

12:00-12:15	<b>[O11A.3] Pressure-induced polymerization on ferrocene-doped C<sub>60</sub> nanosheets and its light irradiation effect</b> H. Gonnokami, K. Kato, H. Murata, M. Tachibana*, <i>Yokohama City University, Japan</i>	12:00-12:30	<b>[Inv.13] A novel method for preparing high-quality two-dimensional hexagonal boron nitride: Ion beam sputtering deposition</b> X.W. Zhang*, H.L. Wang, J.H. Meng, H. Liu, <i>Chinese Academy of Sciences, China</i>
12:15-12:30	<b>[O11A.4] Polymerization of C<sub>60</sub> confined by 1,1,2-trichloroethane under high pressure</b> C. Pei* <sup>1</sup> , M. Feng <sup>2</sup> , L. Wang <sup>1</sup> , <sup>1</sup> <i>Center for High Pressure Science and Technology Advanced Research, China</i> , <sup>2</sup> <i>Jilin University, China</i>		
12:30-14:00	Lunch		
	<b>Session 12: Surfaces &amp; interfaces</b> Chair: C.L. Cheng, <i>National Dong Hwa University, Taiwan</i>		
Room	Auditorium Einstein		
14:00-14:30	<b>[Inv.14] Termination of the diamond surface with silicon and germanium</b> A.K. Schenk <sup>1</sup> , M.J. Sear <sup>1</sup> , A. Tadich <sup>2</sup> , B. Spencer <sup>1</sup> , L. Ley <sup>1,3</sup> , A. Stacey <sup>4</sup> , C.I. Pakes* <sup>1</sup> , <sup>1</sup> <i>La Trobe University, Australia</i> , <sup>2</sup> <i>Australian Synchrotron, Australia</i> , <sup>3</sup> <i>Universität Erlangen, Germany</i> , <sup>4</sup> <i>University of Melbourne, Australia</i>		
14:30-14:45	<b>[O12.1] Enhanced photoelectron emission into vacuum and into ambient environments by amino (-NH<sub>2</sub>) termination of diamond</b> R.J. Hamers*, J. Bandy, S. Li, D. Zhu, <i>University of Wisconsin-Madison, USA</i>		
14:45-15:00	<b>[O12.2] Modulation of protein fouling and interfacial properties at carbon surfaces via immobilization of glycans using aryldiazonium chemistry</b> F. Zen* <sup>1</sup> , J.M. Vasconcelos <sup>1</sup> , J. Andersson <sup>2</sup> , E.M. Scanlan <sup>1</sup> , P.E. Colavita <sup>1</sup> , <sup>1</sup> <i>Trinity College Dublin, Ireland</i> , <sup>2</sup> <i>Insplosion AB, Sweden</i>		
15:00-15:15	<b>[O12.3] Real-time measurement of hole doping by NO<sub>2</sub> and SO<sub>2</sub> molecule adsorption on H-terminated diamond surfaces</b> K. Hanada*, M. Kasu, <i>Saga University, Japan</i>		
15:15-15:30	<b>[O12.4] Microstructure and hole accumulation mechanism of AlN/Diamond(111) heterojunctions prepared by MOVPE</b> M. Imura* <sup>1</sup> , R.G. Banal <sup>1</sup> , M.Y. Liao <sup>1</sup> , J. Liu <sup>1</sup> , Y. Koide <sup>1</sup> , T. Matsumoto <sup>2</sup> , N. Shibata <sup>2</sup> , Y. Ikuhara <sup>2</sup> , <sup>1</sup> <i>National Institute for Materials Science, Japan</i> , <sup>2</sup> <i>The University of Tokyo, Japan</i>		
15:30-16:00	<b>[Inv.15] Atom-by-atom wear of diamond in contact with silica: A quantum-mechanical simulation study</b> G. Moras* <sup>1</sup> , A. Peguiron <sup>1</sup> , M. Walter <sup>1,2</sup> , H. Uetsuka <sup>3</sup> , L. Pastewka <sup>1,4</sup> , M. Moseler <sup>1,2</sup> , <sup>1</sup> <i>Fraunhofer IWM, MicroTribology Center µTC, Germany</i> , <sup>2</sup> <i>University of Freiburg, Germany</i> , <sup>3</sup> <i>Asahi Diamond Industrial Co. Ltd., Japan</i> , <sup>4</sup> <i>Karlsruhe Institute of Technology, Germany</i>		
16:00-17:30	<b>Session 13: Poster session 2 and Refreshment break</b> Chair: YSA Committee		
Room	Foyer Pasteur		
19:00-23:00	<b>Conference dinner</b> Domaine de Verchant		
<b>Thursday, 08 September 2016</b>			
	<b>Session 14: Devices &amp; technology</b> Chair: J. Achard, <i>CNRS- Université Paris 13, France</i>		
Room	Auditorium Einstein		
09:00-09:30	<b>[Inv.16] Diamond optomechanics</b> M. Mitchell <sup>1,2</sup> , B. Khanaliloo <sup>1,2</sup> , D.P. Lake <sup>1,2</sup> , T. Masuda <sup>1</sup> , J.P. Hadden <sup>1</sup> , P.E. Barclay* <sup>1,2</sup> , <sup>1</sup> <i>University of Calgary, Canada</i> , <sup>2</sup> <i>National Institute for Nanotechnology, Canada</i>		
09:30-09:45	<b>[O14.1] Single-crystalline diamond lenses for high-power laser applications</b> V. Zuerbig* <sup>1</sup> , C.J. Widmann <sup>1</sup> , D. Brink <sup>1</sup> , C. Holly <sup>2</sup> , M. Traub <sup>2</sup> , C.E. Nebel <sup>1</sup> , <sup>1</sup> <i>Fraunhofer Institute for Applied Solid State Physics IAF, Germany</i> , <sup>2</sup> <i>Fraunhofer Institute for Laser Technology ILT, Germany</i>		
09:45-10:00	<b>[O14.2] Selective etching of 100 oriented single crystalline substrates for diamond based power electronic applications</b> K. Holc, V. Zuerbig*, W. Mueller-Sebert, C.E. Nebel, <i>Fraunhofer Institute for Applied Solid State Physics, Germany</i>		



10:00-10:15	<b>[O14.3] High-rate anisotropic diamond (100) etching by carbon solid solution reaction into nickel during wet-annealing</b> M. Nagai*, K. Nakanishi, T. Matsumoto, N. Tokuda, T. Inokuma, <i>Kanazawa University, Japan</i>
10:15-10:30	<b>[YSA.6] Integration of diamond on GaN: A thermal and interface study</b> R. Ramaneti* <sup>1,2</sup> , Y. Zhou <sup>4</sup> , S. Korneychuk <sup>3</sup> , J. Anaya Calvo <sup>4</sup> , P. Pobedinskas <sup>1,2</sup> , J. Derluyn <sup>5</sup> , J. Verbeeck <sup>3</sup> , M. Kuball <sup>4</sup> , K. Haenen <sup>1,2</sup> , <sup>1</sup> Hasselt University, Belgium, <sup>2</sup> IMOMECE, IMEC vzw, Belgium, <sup>3</sup> University of Antwerp, Belgium, <sup>4</sup> University of Bristol, UK, <sup>5</sup> EpiGaN b.v., Belgium
10:30-10:45	<b>[O14.4] Photo and/or heat induced large conductivity change in graphene/diamond heterojunctions</b> K. Ueda*, S. Aichi, H. Asano, <i>Nagoya University, Japan</i>
10:45-11:15	Refreshment break Room: Foyer Pasteur
	<b>Session 15: Energy</b> Chair: R.J. Hamers, <i>University of Wisconsin-Madison, USA</i>
Room	Auditorium Einstein
11:15-11:45	<b>[Inv.17] Porous diamond electrodes for thin film supercapacitors</b> E. Scorsone, <i>Commissariat à l'énergie atomique et aux énergies alternatives (CEA), France</i>
11:45-12:00	<b>[O15.1] Metal nanoparticle-embedded porous diamond spherical particle catalysts</b> T. Kondo*, T. Tsujimoto, E. Kai, T. Aikawa, M. Yuasa, <i>Tokyo University of Science, Japan</i>
12:00-12:15	<b>[O15.2] Novel Pt-free nanostructured carbon materials with activity in the oxygen reduction reaction for fundamental studies and applications</b> P.E. Colavita* <sup>1</sup> , S.N. Stamatini <sup>1</sup> , S. Marzorati <sup>2</sup> , J.M. Vasconcelos <sup>1</sup> , M. Longhi <sup>2</sup> , R. Ivanov <sup>3</sup> , I. Hussainova <sup>3</sup> , <sup>1</sup> Trinity College Dublin, Ireland, <sup>2</sup> Università degli Studi di Milano, Italy, <sup>3</sup> Tallinn University of Technology, Estonia
12:15-12:30	<b>[O15.3] Design of attractive carbon-based functional materials by combining atomic layer deposition and solvothermal MOF growth, for application in advanced oxidation process by electro-Fenton</b> R. Esmilaire*, T-X. Le, S. Cerneaux, M. Cretin, M. Drobek, A. Julbe, M. Bechelany, <i>Université de Montpellier, France</i>
12:30-12:45	<b>[O15.4] Development of high power density nuclear microbattery prototype based on diamond Schottky diodes</b> V.S. Bormashov* <sup>1,2</sup> , S.Y. Troschiev <sup>1,2</sup> , S.A. Tarelkin <sup>1,2</sup> , A.P. Volkov <sup>1,2</sup> , D.V. Teteruk <sup>1</sup> , M.S. Kuznetsov <sup>1</sup> , N.V. Kornilov <sup>1</sup> , S.A. Terentiev <sup>1</sup> , V.D. Blank <sup>1,2</sup> , <sup>1</sup> Technological Institute for Superhard and Novel Carbon Materials, Russia, <sup>2</sup> Moscow Institute of Physics and Technology, Russia
12:45-14:15	Lunch
	<b>Session 16: Dopant and defect characterization</b> Chair: S. Yamasaki, <i>National Institute of Advanced Industrial Science and Technology (AIST), Japan</i>
Room	Auditorium Einstein
14:15-14:45	<b>[Inv.18] Developing atom probe tomography as a tool to characterise the atomic-scale composition of doped CVD diamond films</b> T.L. Martin* <sup>1</sup> , S. Drijkoningen <sup>2,3</sup> , M.Z. Othman <sup>4</sup> , P.A.J. Bagot <sup>1</sup> , S. Koelling <sup>5</sup> , P.W. May <sup>4</sup> , K. Haenen <sup>2,3</sup> , M.P. Moody <sup>1</sup> , <sup>1</sup> University of Oxford, UK, <sup>2</sup> Hasselt University, Belgium, <sup>3</sup> Research Institute—IMEC vzw, Belgium, <sup>4</sup> University of Bristol, UK, <sup>5</sup> Technische Universiteit Eindhoven, The Netherlands
14:45-15:00	<b>[O16.1] Isotope tracing and 3D atom-by atom mapping in diamond isotopic homojunctions</b> S. Mukherjee* <sup>1</sup> , H. Watanabe <sup>2</sup> , D. Isheim <sup>3</sup> , D. Seidman <sup>3</sup> , O. Moutanabbir <sup>1</sup> , <sup>1</sup> Ecole Polytechnique de Montreal, Canada, <sup>2</sup> National Institute of Advanced Industrial Science and Technology, Japan, <sup>3</sup> Northwestern University, USA
15:00-15:15	<b>[O16.2] Evidence of linear Zeeman effect for boron doped diamond in high magnetic field</b> S.A. Tarelkin* <sup>1,2</sup> , V.S. Bormashov <sup>1,2</sup> , S.G. Pavlov <sup>4</sup> , D. Kamensky <sup>5</sup> , M.S. Kuznetsov <sup>1</sup> , S.A. Terentiev <sup>1</sup> , A.S. Galkin <sup>1</sup> , H-W. Hubers <sup>4,6</sup> , <sup>1</sup> Technological Institute for Superhard and Novel Carbon Materials, Russia, <sup>2</sup> Moscow Institute of Physics and Technology, Russia, <sup>3</sup> National University of Science and Technology MISIS, Russia, <sup>4</sup> German Aerospace Center (DLR), Germany, <sup>5</sup> Radboud University Nijmegen, The Netherlands, <sup>6</sup> Humboldt-Universität zu Berlin, Germany
15:15-15:30	<b>[O16.3] Impact of HPHT substrates imperfections on the properties of phosphorus-doped CVD diamond layers</b> P. Pobedinskas* <sup>1,2</sup> , P. Ščajej <sup>3</sup> , T.N. Tran Thi <sup>4</sup> , A. Lazea-Stoyanova <sup>5</sup> , K. Jarašiūnas <sup>3</sup> , K. Haenen <sup>1,2</sup> , <sup>1</sup> Hasselt University, Belgium, <sup>2</sup> IMEC vzw, IMOMECE, Belgium, <sup>3</sup> Vilnius University, Lithuania, <sup>4</sup> European Synchrotron Radiation Facility, France, <sup>5</sup> National Institute for Laser, Plasma and Radiation Physics, Romania
15:30-15:45	<b>[O16.4] Advanced spectroscopic characterization of optical defects in thick CVD diamond layers grown with addition of moderate amounts of N<sub>2</sub></b> E. Biermans* <sup>1</sup> , E. Barrie <sup>1</sup> , A. Tallaire <sup>2</sup> , J. Achard <sup>2</sup> , A. Stesmans <sup>3</sup> , A. Anthonis <sup>1</sup> , <sup>1</sup> HRD Antwerp, Belgium,

	<sup>2</sup> Université Paris 13, France, <sup>3</sup> University of Leuven, Belgium
15:45-16:00	<b>[O16.5] Investigation of defects in diamonds with VUV photoluminescence using synchrotron source</b> H-C. Lu*, Y-C. Peng, M-Y. Lin, C-L. Chou, J-I. Lo, B-M. Cheng, <i>National Synchrotron Radiation Research Center, Taiwan</i>
16:00-16:30	Refreshment break Room: Foyer Pasteur
	<b>Session 17: Diamond devices</b> Chair: S. Koizumi, <i>National Institute for Materials Science (NIMS), Japan</i>
Room	Auditorium Einstein
16:30-16:45	<b>[O17.1] Single-particle diamond membrane detector based on secondary electron emission for radiobiological applications</b> M.T. Pomorski* <sup>1</sup> , P. Barberet <sup>2,3</sup> , G. Claverie <sup>2,3</sup> , C. Mer-Calfati <sup>1</sup> , S. Saada <sup>1</sup> , <sup>1</sup> CEA-LIST, <i>Diamond Sensor Laboratory, France</i> , <sup>2</sup> Université de Bordeaux, France, <sup>3</sup> CNRS, France
16:45-17:00	<b>[O17.2] Progress in 3D diamond detector development for tracking and dosimetry measurements</b> A. Oh, I. Haughton*, F. Munoz Sanchez, G. Forcolin, S. Murphy, <i>The University of Manchester, UK</i>
17:00-17:15	<b>[O17.3] Transient current induced in thin film diamonds by swift heavy ions</b> S-I. Sato* <sup>1</sup> , T. Makino <sup>1</sup> , T. Ohshima <sup>1</sup> , T. Kamiya <sup>1</sup> , W. Kada <sup>2</sup> , V. Grilj <sup>3</sup> , N. Skukan <sup>3</sup> , M. Jakšić <sup>3</sup> , M. Pomorski <sup>5</sup> , G. Vizkelethy <sup>4</sup> , <sup>1</sup> Japan National Institutes of Quantum and Radiological Science and Technology, Japan, <sup>2</sup> Gunma University, Japan, <sup>3</sup> Ruder Boškovic Institute, Croatia, <sup>4</sup> Sandia National Laboratories, USA, <sup>5</sup> CEA-LIST, France
17:15-17:30	<b>[O17.4] Integrated temperature sensor with diamond Schottky diodes using a thermosensitive parameter</b> G. Perez* <sup>1,2</sup> , N. Rouger <sup>1,2</sup> , P. Lefranc <sup>1,2</sup> , P-O. Jeannin <sup>1,2</sup> , Y. Avenas <sup>1,2</sup> , G. Chicot <sup>1,2</sup> , D. Eon <sup>1,2</sup> , <sup>1</sup> Université Grenoble Alpes, France, <sup>2</sup> CNRS, France
17:30-17:45	<b>[O17.5] Fabrication of diamond rectenna devices for wireless power transmission</b> M. Kasu* <sup>1,2</sup> , T. Oishi <sup>1</sup> , N. Kawano <sup>1</sup> , A. Miyachi <sup>2</sup> , S. Kawasaki <sup>1</sup> , <sup>1</sup> Saga University, Japan, <sup>2</sup> Japan Aerospace Exploration Agency, Japan
17:45-18:00	Closing ceremony – <b>K. Haenen</b> , <i>Hasselt University and IMEC vzw, Belgium</i>